

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	44	(polysilicon) and (oxygen with sink)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:39
L6	1343	257/412.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:40
L7	1602	257/751.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:40
L8	790	257/754.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:40
L9	402	257/761.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:40
L10	517	257/767.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:41
L11	2694	257/773.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:41

## EAST Search History

L12	6706	I6 or I7 or I8 or I9 or I10 or I11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:43
L13	0	metal with polysilicon with contact with barrier with opening with insulating with plurality with absorbing with oxygen with conductive.clms.	US-PGPUB	OR	ON	2007/04/15 21:43
S1	17	(polysilicon with barrier) and (oxygen with absorbing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 21:33
S2	623	gate and (polysilicon with barrier) and (sidewall with nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 17:19
S3	9	S2 and (gate with (platinum or iridium or ruthenium or rhodium)) and (barrier with (nitride or carbide or boride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 06:42
S4	12	S2 and (gate with (platinum or iridium or ruthenium or rhodium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 17:30
S5	32	(polysilicon with gate) and (gate with (platinum or iridium or ruthenium or rhodium)) and (gate with barrier with (nitride or carbide or boride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 17:40
S6	623	gate and (polysilicon with barrier) and (sidewall with nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 06:42
S7	9	S6 and (gate with (platinum or iridium or ruthenium or rhodium)) and (barrier with (nitride or carbide or boride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 06:43

## EAST Search History

S8	8	(polysilicon with barrier with platinum with (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 05:57
S9	4	"6677632"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 07:56
S10	3467	257/296.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/16 14:54
S11	9	"6583460"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 11:34
S12	13	"6373088"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 11:53
S13	7	(US-20010026004-\$ or US-20020079548-\$).did. or (US-6730581-\$ or US-6187686-\$ or US-6235579-\$ or US-6677632-\$ or US-6373088-\$).did.	US-PGPUB; USPAT	OR	ON	2006/05/12 12:19
S14	4	S13 and memory and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 12:20
S15	890	438/652.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 07:51
S16	262	(polysilicon with gate) and ((control adj gate) with sidewall with nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 07:58
S17	3	(polysilicon with (barrier adj layer)) and ((control adj gate) with sidewall with nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 07:59